

JULY 1975

DIGITAL 8000 SERIES TTL/MEMORY

### DESCRIPTION

The 82S27 is a Bipolar 1024-Bit Read Only Memory, organized as 256 words by 4 bits per word. It is Field-Programmable, which means that custom patterns are immediately available by following the fusing procedure given in this data sheet. The standard 82S27 is supplied with all outputs at logical "0". Outputs are programmed to a logic "1" level at any specified address by fusing a Ni-Cr link matrix.

The 82S27 is fully TTL compatible, and includes on-chip decoding, two chip enable inputs, and open collector outputs for ease of memory expansion.

The 82S27 is available in the commercial temperature range. For the commercial temperature range (0°C to +75°C) specify N82S27, F.

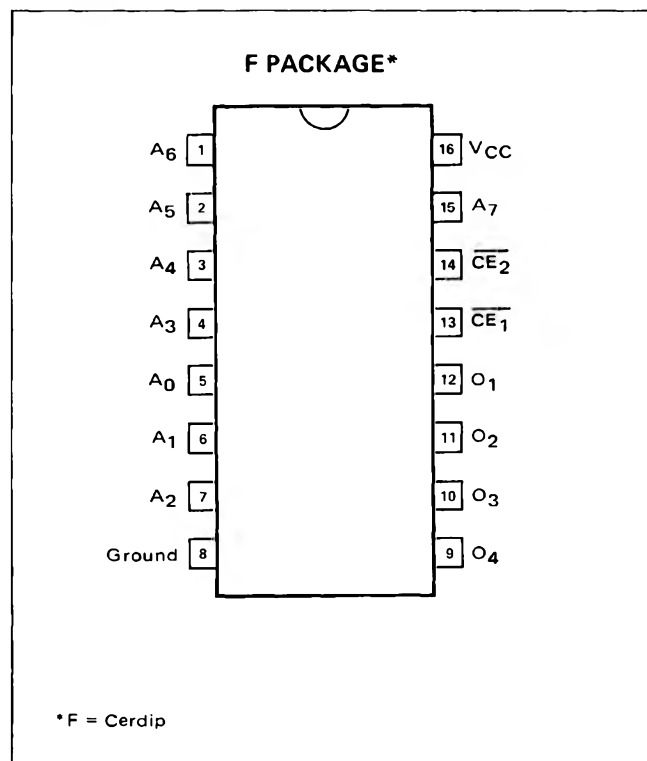
### FEATURES

- ORGANIZATION — 256 X 4
- ADDRESS ACCESS TIME — 40ns, MAXIMUM
- POWER DISSIPATION — 0.6mW/BIT, TYPICAL
- INPUT LOADING — 1.6mA, MAXIMUM
- TWO CHIP ENABLE INPUTS
- ON-CHIP ADDRESS DECODING
- OPEN COLLECTOR OUTPUTS
- NO SEPARATE "FUSING" PINS
- UNPROGRAMMED OUTPUTS ARE "0" LEVEL
- 16-PIN CERAMIC DIP

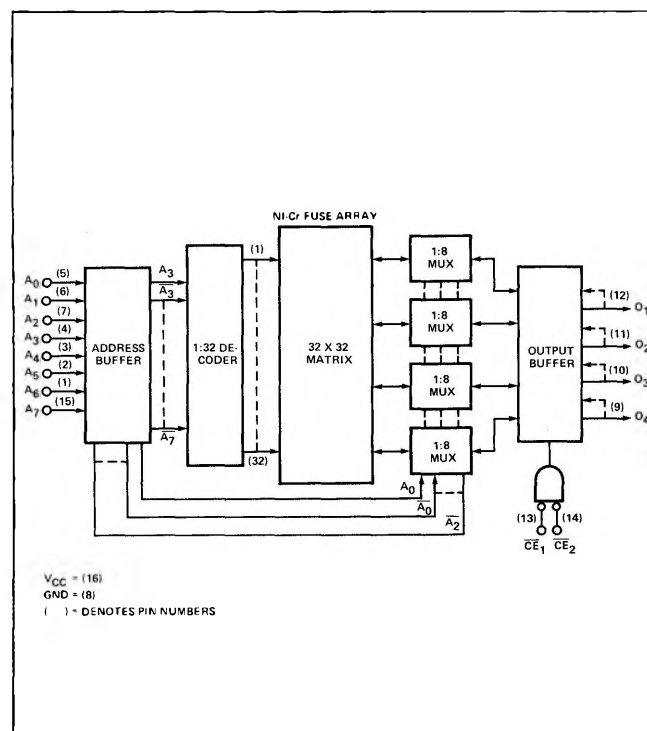
### APPLICATIONS

PROTOTYPING/VOLUME PRODUCTION  
SEQUENTIAL CONTROLLERS  
MICROPROGRAMMING  
HARDWIRED ALGORITHMS  
CONTROL STORE  
RANDOM LOGIC  
CODE CONVERSION

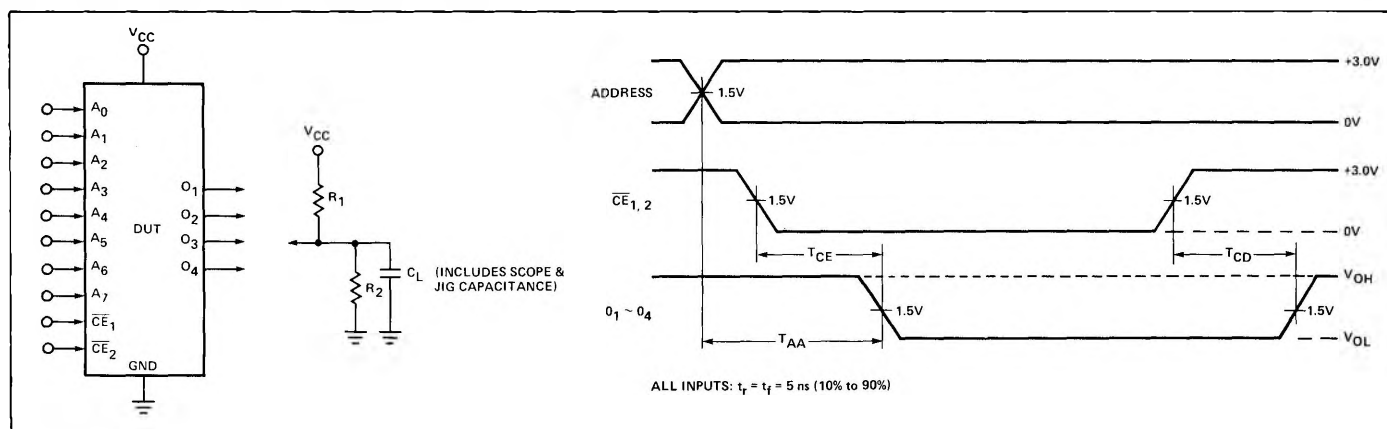
### PIN CONFIGURATION



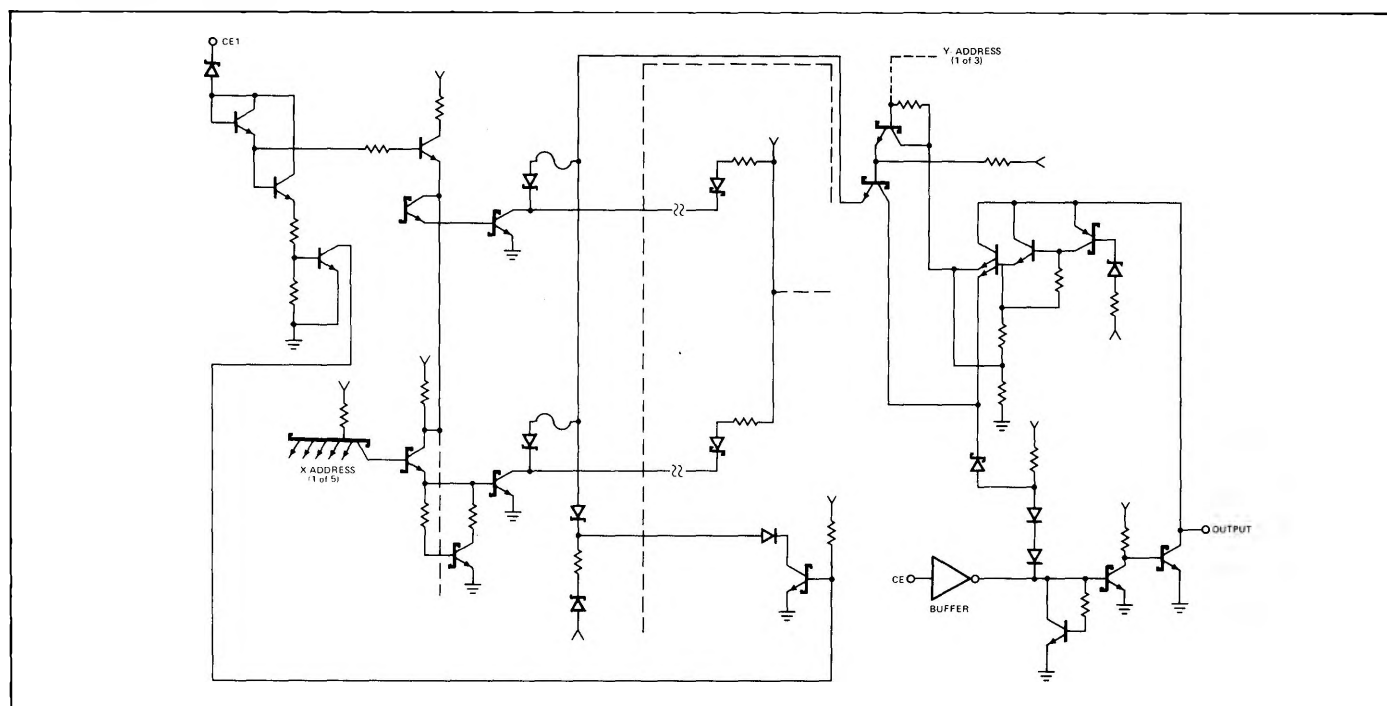
### BLOCK DIAGRAM



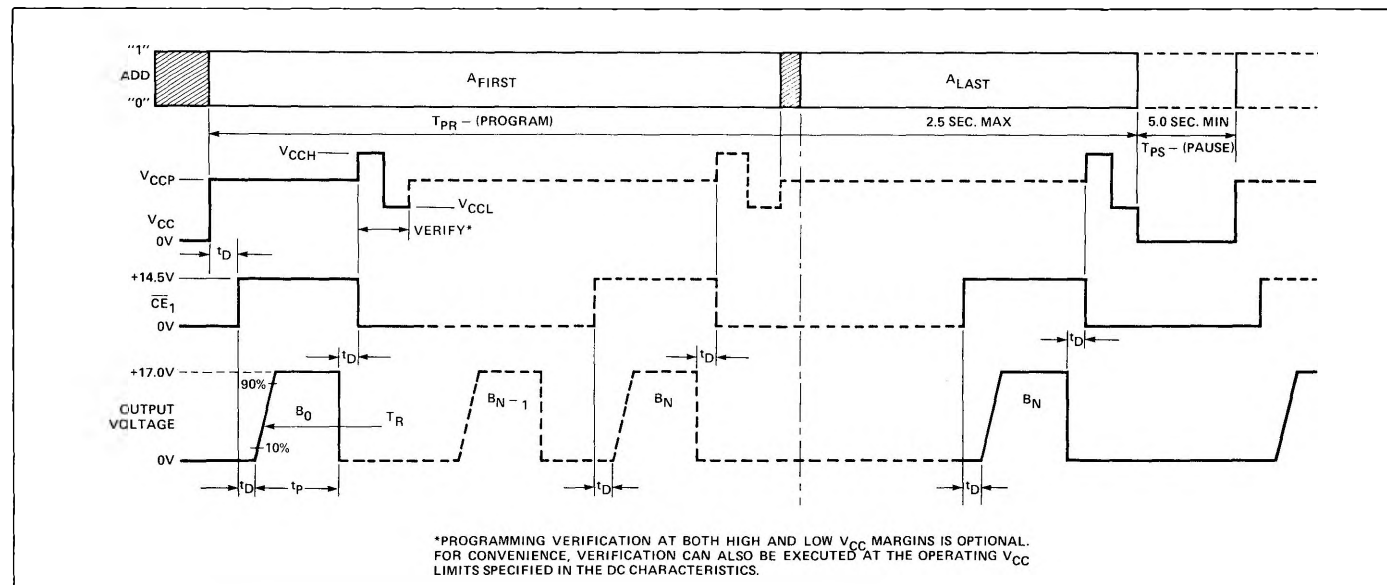
## AC TEST FIGURE AND WAVEFORM



## TYPICAL FUSING PATH



## TYPICAL PROGRAMMING SEQUENCE



## ABSOLUTE MAXIMUM RATINGS

PARAMETER		RATING	UNIT
$V_{CC}$	Power Supply Voltage	+7	Vdc
$V_{IN}$	Input Voltage	+5.5	Vdc
$V_{OH}$	High Level Output Voltage	+5.5	Vdc
$T_A$	Operating Temperature Range	0° to +75°	°C
$T_{stg}$	Storage Temperature Range	-65° to +150°	°C

ELECTRICAL CHARACTERISTICS 0°C ≤  $T_A$  ≤ +75°C, 4.75V ≤  $V_{CC}$  ≤ 5.25V

PARAMETER	TEST CONDITIONS <sup>1</sup>	LIMITS			UNIT
		MIN	TYP <sup>2</sup>	MAX	
$V_{OL}$	"0" Output Voltage	2.0	0.45	0.50	V
$I_{OLK}$	Output Leakage Current			100	μA
$I_{IH}$	"1" Input Current			40	μA
	$V_{IN} = 2.4V$			1	mA
	$V_{IN} = 5.5V$				
$I_{IL}$	"0" Input Current			-1.6	mA
$V_{IL}$	"0" Level Input Voltage			.80	V
$V_{IH}$	"1" Level Input Voltage				V
$I_{CC}$	$V_{CC}$ Supply Current		120	140	mA
$V_{IC}$	Input Clamp Voltage		-1.0	-1.5	V
$C_{IN}$	Input Capacitance		5		pF
$C_{OUT}$	Output Capacitance		8		pF

SWITCHING CHARACTERISTICS 0°C ≤  $T_A$  ≤ +75°C, 4.75V ≤  $V_{CC}$  ≤ 5.25V

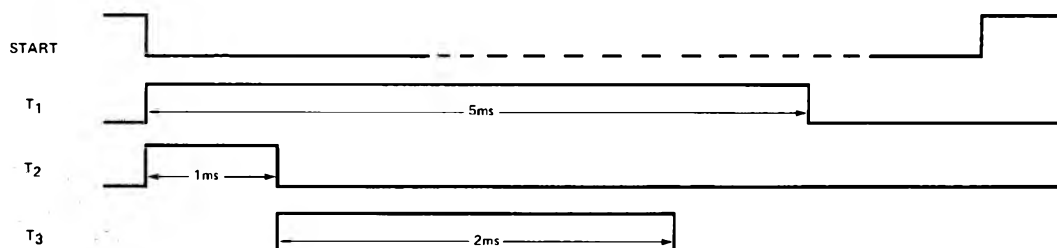
PARAMETER	TEST CONDITIONS	LIMITS			UNIT
		MIN	TYP <sup>2</sup>	MAX	
Propagation Delay					
T <sub>AA</sub>	Address to Output	C <sub>L</sub> = 30pF	30	40	ns
T <sub>CD</sub>	Chip Disable to Output	R <sub>1</sub> = 270Ω	15	20	ns
T <sub>CE</sub>	Chip Enable to Output	R <sub>2</sub> = 600Ω	15	20	ns

## NOTES:

1. Positive current is defined as into the terminal referenced.
2. Typical values are at  $V_{CC} = 5.0V$ ,  $T_A = +25^\circ C$ .



## TIMING SEQUENCE



**PROGRAMMING SPECIFICATIONS** (Testing of these limits may cause programming of device.)  $T_A = +25^\circ\text{C}$ 

PARAMETER	TEST CONDITIONS	LIMITS			UNIT
		MIN	TYP	MAX	
Power Supply Voltage					
V <sub>CCP</sub> <sup>1</sup> To Program	I <sub>CCP</sub> = 300 ± 50mA (Transient or steady state)	5.0		5.25	V
V <sub>CCH</sub> Upper Verify Limit		5.0	5.25	5.5	V
V <sub>CCL</sub> Lower Verify Limit		4.5	4.75	5.0	V
V <sub>S</sub> <sup>3</sup> Verify Threshold		0.9	1.0	1.1	V
I <sub>CCP</sub> Programming Supply Current	V <sub>CCP</sub> = +5.0 ± 0.25V	250	300	350	mA
Input Voltage					
V <sub>IH</sub> Logical "1" (Except $\overline{CE}_1$ )		3.0		5.0	V
V <sub>IN</sub> Program Level ( $\overline{CE}_1$ Only)		14.0	14.5	15.0	V
V <sub>IL</sub> Logical "0"		0	0.4	0.5	V
Input Current					
I <sub>IH</sub> Logical "1"	V <sub>IH</sub> = +3.0V			100	μA
I <sub>IL</sub> Logical "0"	V <sub>IL</sub> = +0.5V			-1.6	mA
I <sub>IN</sub> Program Level ( $\overline{CE}_1$ Only)	V <sub>IN</sub> = +15.0V			15	mA
V <sub>OUT</sub> <sup>2</sup> Output Programming Voltage	I <sub>OUT</sub> = 115 ± 10mA (Transient or steady state)	16.5	17.0	17.5	V
I <sub>OUT</sub> Output Programming Current	V <sub>OUT</sub> = +17.0 ± 0.5V	105	115	125	mA
T <sub>R</sub> <sup>5</sup> Output Pulse Rise Time		0.2		0.5	μs
t <sub>p</sub> Programming Pulse Width		1		2	ms
t <sub>D</sub> Pulse Sequence Delay		10			μs
T <sub>PR</sub> Programming Time	V <sub>CC</sub> = V <sub>CCP</sub>			2.5	sec
T <sub>PS</sub> Programming Pause	V <sub>CC</sub> = 0V	5			sec
$\frac{T_{PR}^4}{T_{PR}+T_{PS}}$ Programming Duty Cycle				33	%

**PROGRAMMING PROCEDURE**

The 82S27 is shipped with all bits at logical "0" (low). To write logical "1", proceed as follows:

**SET-UP**

- Apply GND to pin 12.
- Terminate all device outputs with a  $10\text{k}\Omega$  resistor to  $V_{CC}$ .
- Set  $\overline{CE}_2$  to logic "0".

**PROGRAM-VERIFY SEQUENCE**

- Step 1 Raise  $V_{CC}$  to  $V_{CCP}$ , and address the word to be programmed by applying TTL "1" and "0" logic levels to the device address inputs.
- Step 2 After  $10\mu\text{s}$  delay, apply to  $\overline{CE}_1$  (pin 13) a voltage source of  $14.5 \pm 0.5\text{V}$ , with 15mA sourcing current capability.

Step 3 After  $10\mu\text{s}$  delay, apply a voltage source of  $+17.0 \pm 0.5\text{V}$  to the output to be programmed. The source must have a current limit of 115mA. Program one output at the time.

Step 4 After  $10\mu\text{s}$  delay, remove  $+17.0\text{V}$  supply from programmed output.

Step 5 To verify programming, after  $10\mu\text{s}$  delay, return  $\overline{CE}_1$  to 0V. Raise  $V_{CC}$  to  $V_{CCH} = +5.25 \pm .25\text{V}$ . The programmed output should remain in the "1" state. Again, lower  $V_{CC}$  to  $V_{CCL} = +4.75 \pm .25\text{V}$ , and verify that the programmed output remains in the "1" state.

Step 6 Raise  $V_{CC}$  to  $V_{CCP}$ , and repeat steps 2 through 5 to program other bits at the same address.

Step 7 Repeat steps 1 through 6 to program all other address locations.

**NOTES:**

1. Bypass  $V_{CC}$  to GND with a  $0.01\mu\text{F}$  capacitor to reduce voltage spikes.
2. Care should be taken to insure the  $17 \pm 0.5\text{V}$  output voltage is maintained during the entire fusing cycle. The recommended supply is a constant current source clamped at the specified voltage limit.
3.  $V_S$  is the sensing threshold of the PROM output voltage for a programmed bit. It normally constitutes the reference voltage applied to a comparator circuit to verify a successful fusing attempt.
4. Continuous fusing for an unlimited time is also allowed, provided that a 33% duty cycle is maintained. This may be accomplished by following each Program Verify cycle with a Rest period ( $V_{CC} = 0\text{V}$ ) of 4ms.
5. Measured with a 1k dummy load connected across the fusing source.